



Edition 4.0 2025-09

INTERNATIONAL STANDARD

Semiconductor devices - iTeh Standards
Part 6: Discrete devices - Thyristors
(https://standards.iteh.ai)

Document Preview

<u>1EC 60747-6:2025</u>

https://standards.iteh.ai/catalog/standards/iec/4d5c1851-cb8a-4c9b-8f2e-71a8dfd03ef2/iec-60747-6-2025



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